Abstracts

High Power Pulsed IMPATT Oscillator Near 140 GHz

Y.C. Ngan and E.M. Nakaji. "High Power Pulsed IMPATT Oscillator Near 140 GHz." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 73-74.

IMPATT diodes with a double drift p+-p-n-n+ doping profile were fabricated and tested for high power pulsed operation. Using a pulse width of 100 ns and a 0.5% duty factor, a peak output power of 3.0W with 2.8% conversion efficiency has been measured at 140 GHz.

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